

**CoolSiC™ Hybrid Discrete - TRENCHSTOP™ 5 S5 IGBT co-packed with full-rated 6th generation CoolSiC™ diode**

**Features**

- $V_{CE} = 650\text{ V}$
- $I_C = 75\text{ A}$
- Ultra-low switching losses due to the combination of TRENCHSTOP™ 5 and CoolSiC™ technology as well as the Kelvin emitter pin
- Very low on-state losses
- Benchmark efficiency in hard switching topologies
- Plug-and-play replacement of pure silicon devices
- Simplified PCB design due to the optimized pin-out of the four-pin package
- Improved wave soldering quality due to the increased clearance of the Kelvin emitter and gate pins
- Maximum junction temperature  $T_{vjmax} = 175^\circ\text{C}$
- Qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>



- Lead-free
- Green
- Halogen-free
- RoHS

**Potential applications**

- Industrial SMPS
- Industrial UPS
- Solar string inverter
- Energy storage
- Charger

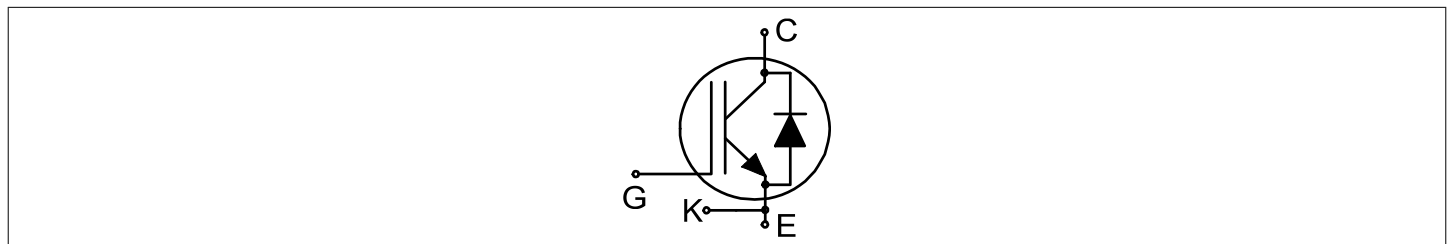
**Product validation**

- Qualified for applications listed above based on the test conditions in the relevant tests of JEDEC20/22

**Description**

Package pin definition:

- Pin C & backside - collector
- Pin E - emitter
- Pin K - Kelvin emitter
- Pin G - gate



Type	Package	Marking
IKZA75N65SS5	PG-TO247-4-3	K75ESS5

## Table of contents

	<b>Description</b> .....	1
	<b>Features</b> .....	1
	<b>Potential applications</b> .....	1
	<b>Product validation</b> .....	1
	<b>Table of contents</b> .....	2
<b>1</b>	<b>Package</b> .....	3
<b>2</b>	<b>IGBT</b> .....	3
<b>3</b>	<b>Diode</b> .....	6
<b>4</b>	<b>Characteristics diagrams</b> .....	7
<b>5</b>	<b>Package outlines</b> .....	13
<b>6</b>	<b>Testing conditions</b> .....	14
	<b>Revision history</b> .....	15
	<b>Disclaimer</b> .....	16

## 1 Package

**Table 1** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	$L_E$			13.0		nH
Storage temperature	$T_{stg}$		-55		150	°C
Soldering temperature		wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	$M$	M3 screw Maximum of mounting process: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W

## 2 IGBT

**Table 2** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Collector-emitter voltage	$V_{CE}$	$T_{vj} \geq 25\text{ °C}$	650	V	
DC collector current, limited by $T_{vjmax}$	$I_C$	limited by bondwire	$T_c = 25\text{ °C}$	80	A
			$T_c = 100\text{ °C}$	80	
Pulsed collector current, $t_p$ limited by $T_{vjmax}$	$I_{Cpulse}$		300	A	
Turn-off safe operating area		$V_{CE} \leq 650\text{ V}$ , $t_p = 1\text{ }\mu\text{s}$ , $T_{vj} \leq 175\text{ °C}$	300	A	
Gate-emitter voltage	$V_{GE}$		$\pm 20$	V	
Transient gate-emitter voltage	$V_{GE}$	$t_p \leq 10\text{ }\mu\text{s}$ , $D < 0.01$	$\pm 30$	V	
Power dissipation	$P_{tot}$		$T_c = 25\text{ °C}$	395	W
			$T_c = 100\text{ °C}$	197	

**Table 3** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C = 75\text{ A}$ , $V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$		1.35	1.7	V
			$T_{vj} = 125\text{ °C}$		1.55		
			$T_{vj} = 175\text{ °C}$		1.65		
Gate-emitter threshold voltage	$V_{GEth}$	$I_C = 0.75\text{ mA}$ , $V_{CE} = V_{GE}$	3.2	4	4.8	V	

(table continues...)

**Table 3 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Zero gate-voltage collector current	$I_{CES}$	$V_{CE} = 650 \text{ V}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$			1900	$\mu\text{A}$
			$T_{vj} = 175 \text{ }^\circ\text{C}$		3000		
Zero gate-voltage collector current	$I_{CES}$	$V_{CE} = 480 \text{ V}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$			50	$\mu\text{A}$
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0 \text{ V}, V_{GE} = 20 \text{ V}$				100	nA
Transconductance	$g_{fs}$	$I_C = 75 \text{ A}, V_{CE} = 20 \text{ V}$		100			S
Input capacitance	$C_{ies}$	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 250 \text{ kHz}$		4000			pF
Output capacitance	$C_{oes}$	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 250 \text{ kHz}$		785			pF
Reverse transfer capacitance	$C_{res}$	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 250 \text{ kHz}$		15			pF
Gate charge	$Q_G$	$I_C = 75 \text{ A}, V_{GE} = 15 \text{ V}, V_{CC} = 520 \text{ V}$		164			nC
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 400 \text{ V}, V_{GE} = 0/15 \text{ V}, R_{Gon} = 5.6 \text{ } \Omega, R_{Goff} = 5.6 \text{ } \Omega, L_\sigma = 30 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$		22		ns
			$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 37.5 \text{ A}$		20		
			$T_{vj} = 150 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$		21		
			$T_{vj} = 150 \text{ }^\circ\text{C}, I_C = 37.5 \text{ A}$		20		
Rise time (inductive load)	$t_r$	$V_{CC} = 400 \text{ V}, V_{GE} = 0/15 \text{ V}, R_{Gon} = 5.6 \text{ } \Omega, R_{Goff} = 5.6 \text{ } \Omega, L_\sigma = 30 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$		12		ns
			$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 37.5 \text{ A}$		7		
			$T_{vj} = 150 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$		14		
			$T_{vj} = 150 \text{ }^\circ\text{C}, I_C = 37.5 \text{ A}$		8		
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 400 \text{ V}, V_{GE} = 0/15 \text{ V}, R_{Gon} = 5.6 \text{ } \Omega, R_{Goff} = 5.6 \text{ } \Omega, L_\sigma = 30 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$		145		ns
			$T_{vj} = 25 \text{ }^\circ\text{C}, I_C = 37.5 \text{ A}$		155		
			$T_{vj} = 150 \text{ }^\circ\text{C}, I_C = 75 \text{ A}$		172		
			$T_{vj} = 150 \text{ }^\circ\text{C}, I_C = 37.5 \text{ A}$		200		

(table continues...)

**Table 3 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Fall time (inductive load)	$t_f$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{Gon} = 5.6\ \Omega,$ $R_{Goff} = 5.6\ \Omega, L_{\sigma} = 30\text{ nH},$ $C_{\sigma} = 30\text{ pF}$	$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		20		ns
			$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		25		
			$T_{vj} = 150\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		27		
			$T_{vj} = 150\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		42		
Turn-on energy	$E_{on}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{Gon} = 5.6\ \Omega,$ $R_{Goff} = 5.6\ \Omega, L_{\sigma} = 30\text{ nH},$ $C_{\sigma} = 30\text{ pF}$	$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		0.24		mJ
			$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		0.13		
			$T_{vj} = 150\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		0.34		
			$T_{vj} = 150\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		0.18		
Turn-off energy	$E_{off}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{Gon} = 5.6\ \Omega,$ $R_{Goff} = 5.6\ \Omega, L_{\sigma} = 30\text{ nH},$ $C_{\sigma} = 30\text{ pF}$	$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		0.75		mJ
			$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		0.42		
			$T_{vj} = 150\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		1.26		
			$T_{vj} = 150\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		0.75		
Total switching energy	$E_{ts}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{Gon} = 5.6\ \Omega,$ $R_{Goff} = 5.6\ \Omega, L_{\sigma} = 30\text{ nH},$ $C_{\sigma} = 30\text{ pF}$	$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		0.99		mJ
			$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		0.55		
			$T_{vj} = 150\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		1.6		
			$T_{vj} = 150\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		0.93		
IGBT thermal resistance, junction-case	$R_{th(j-c)}$				0.38	K/W	
Operating junction temperature	$T_{vj}$		-40		175	$^{\circ}\text{C}$	

### 3 Diode

**Table 4** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	$V_{RRM}$	$T_{vj} \geq 25\text{ °C}$	650	V	
Diode forward current, limited by $T_{vjmax}$	$I_F$	limited by bondwire	$T_c = 25\text{ °C}$	80	A
			$T_c = 100\text{ °C}$	57	
Diode pulsed current, $t_p$ limited by $T_{vjmax}$ <sup>1)</sup>	$I_{Fpulse}$		225	A	

1) Pulse current level depends on  $T_{vj}$  of diode chip, see also Fig. "Maximum pulse current as a function of junction temperature"

**Table 5** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Diode forward voltage	$V_F$	$I_F = 60\text{ A}$	$T_{vj} = 25\text{ °C}$	1.35	1.5	V
			$T_{vj} = 125\text{ °C}$	1.55		
			$T_{vj} = 175\text{ °C}$	1.65		
Diode thermal resistance, junction-case	$R_{th(j-c)}$				0.68	K/W
Operating junction temperature	$T_{vj}$		-40		175	°C

**Note:** For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

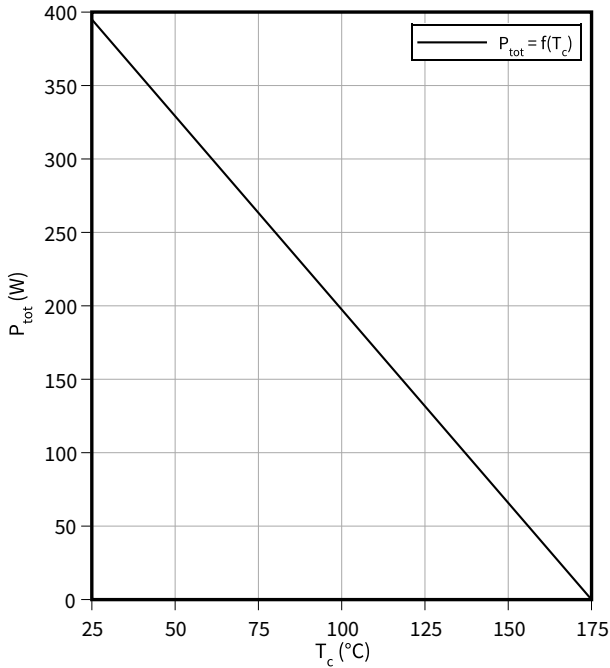
Electrical Characteristic at  $T_{vj} = 25\text{ °C}$ , unless otherwise specified.

Dynamic test circuit, parasitic inductance  $L_\sigma$ , parasitic capacitor  $C_\sigma$  from Fig. E. Energy losses include "tail" and diode reverse recovery.

## 4 Characteristics diagrams

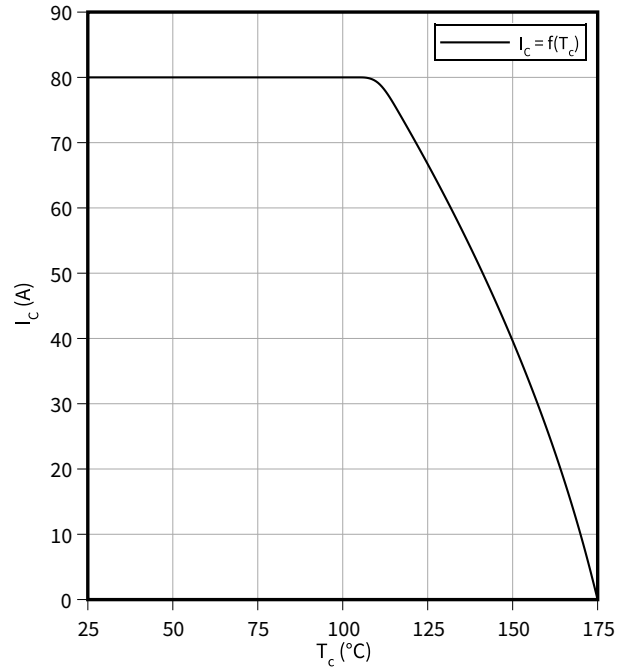
### Power dissipation as a function of case temperature

$P_{tot} = f(T_c)$   
 $T_{vj} \leq 175\text{ °C}$



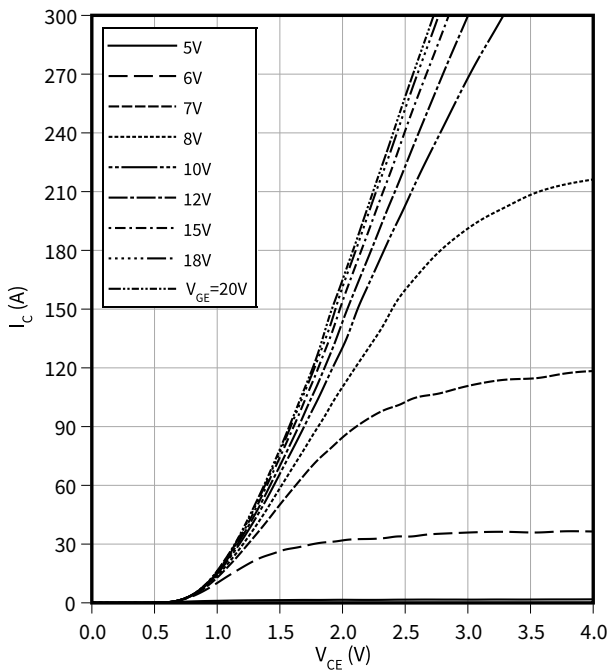
### Collector current as a function of case temperature

$I_C = f(T_c)$   
 $T_{vj} \leq 175\text{ °C}, V_{GE} \geq 15\text{ V}$



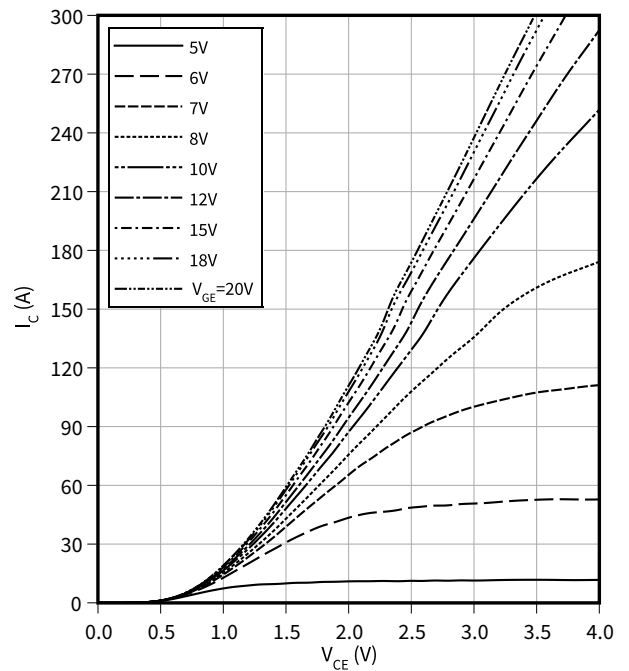
### Typical output characteristic

$I_C = f(V_{CE})$   
 $T_{vj} = 25\text{ °C}$



### Typical output characteristic

$I_C = f(V_{CE})$   
 $T_{vj} = 150\text{ °C}$

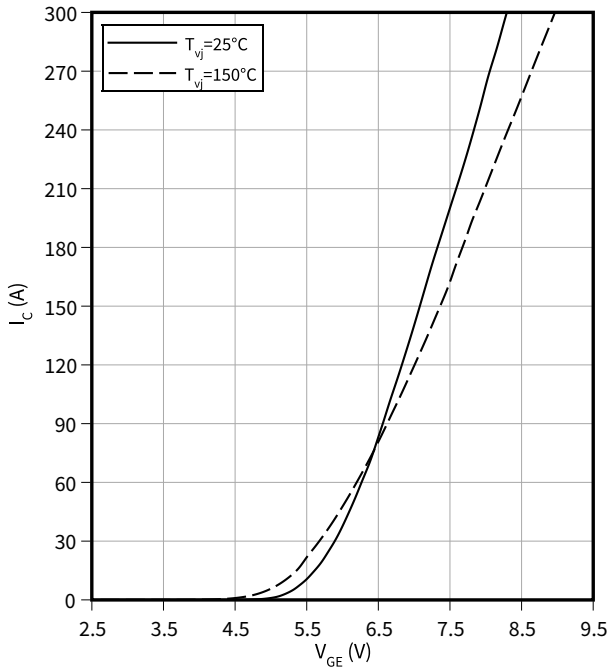


4 Characteristics diagrams

**Typical transfer characteristic**

$I_C = f(V_{GE})$

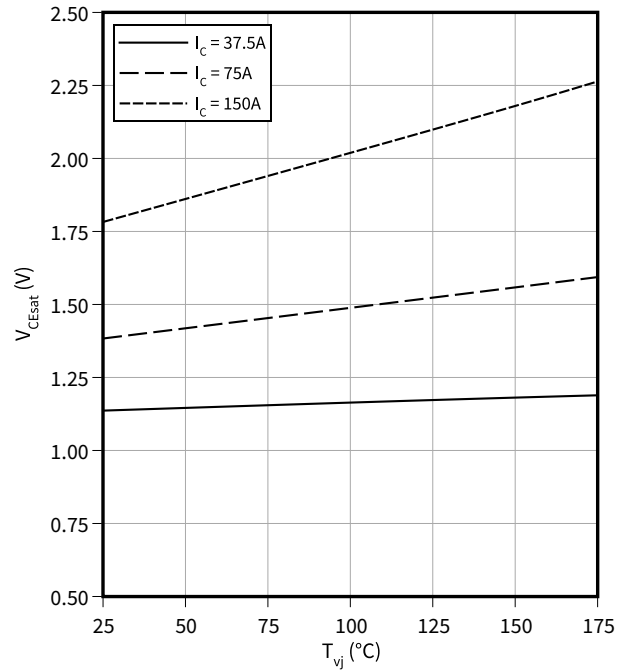
$V_{CE} = 20\text{ V}$



**Typical collector-emitter saturation voltage as a function of junction temperature**

$V_{CEsat} = f(T_{vj})$

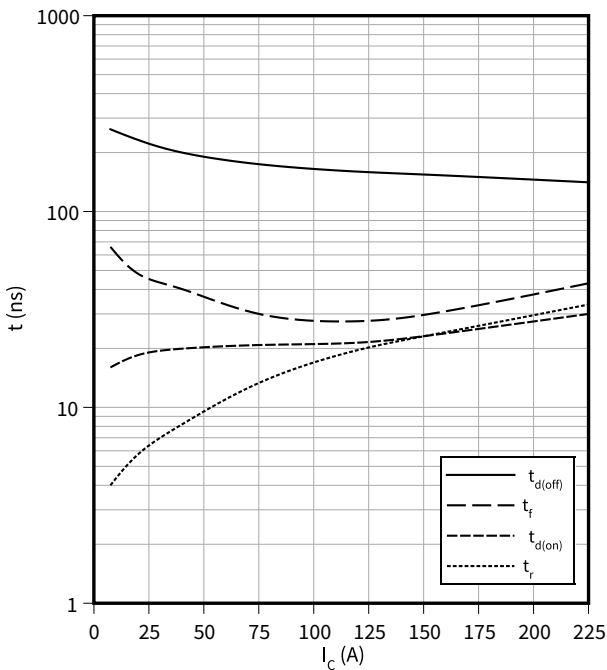
$V_{GE} = 15\text{ V}$



**Typical switching times as a function of collector current**

$t = f(I_C)$

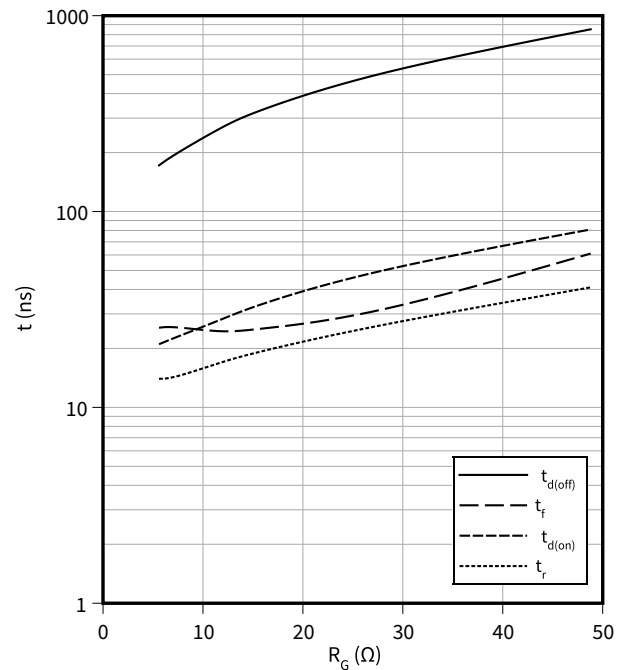
$V_{CC} = 400\text{ V}, T_{vj} = 150^\circ\text{C}, V_{GE} = 0/15\text{ V}, R_G = 5.6\ \Omega$



**Typical switching times as a function of gate resistor**

$t = f(R_G)$

$I_C = 75\text{ A}, V_{CC} = 400\text{ V}, T_{vj} = 150^\circ\text{C}, V_{GE} = 0/15\text{ V}$



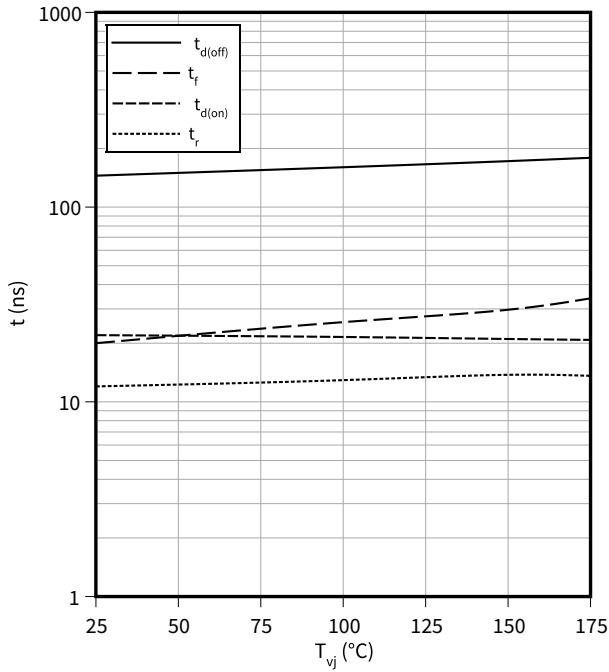


4 Characteristics diagrams

**Typical switching times as a function of junction temperature**

$t = f(T_{vj})$

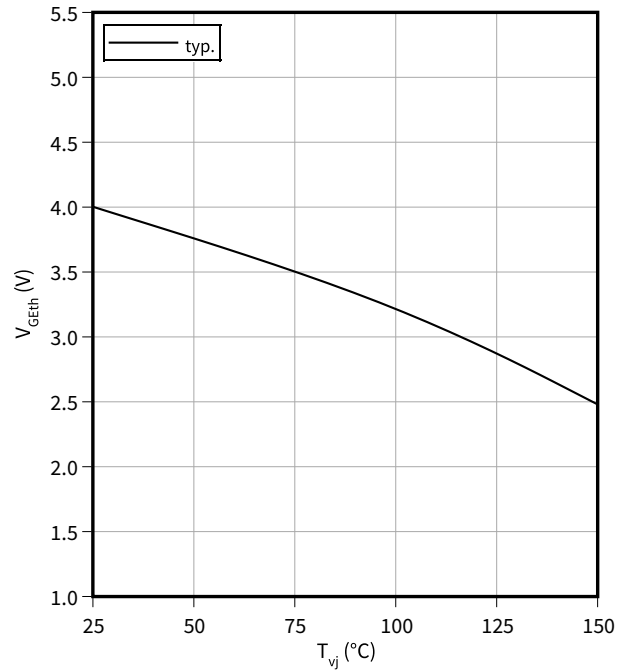
$I_C = 75 \text{ A}$ ,  $V_{CC} = 400 \text{ V}$ ,  $V_{GE} = 0/15 \text{ V}$ ,  $R_G = 5.6 \Omega$



**Gate-emitter threshold voltage as a function of junction temperature**

$V_{GEth} = f(T_{vj})$

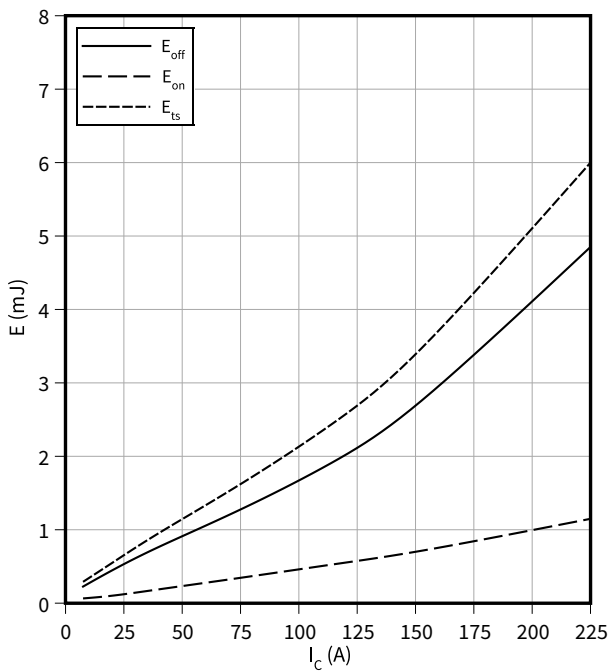
$I_C = 0.75 \text{ mA}$



**Typical switching energy losses as a function of collector current**

$E = f(I_C)$

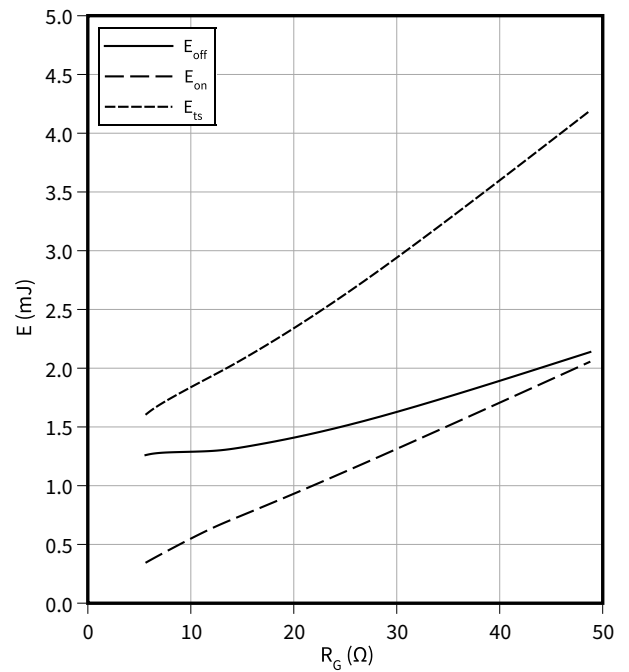
$V_{CC} = 400 \text{ V}$ ,  $T_{vj} = 150 \text{ °C}$ ,  $V_{GE} = 0/15 \text{ V}$ ,  $R_G = 5.6 \Omega$



**Typical switching energy losses as a function of gate resistor**

$E = f(R_G)$

$I_C = 75 \text{ A}$ ,  $V_{CC} = 400 \text{ V}$ ,  $T_{vj} = 150 \text{ °C}$ ,  $V_{GE} = 0/15 \text{ V}$

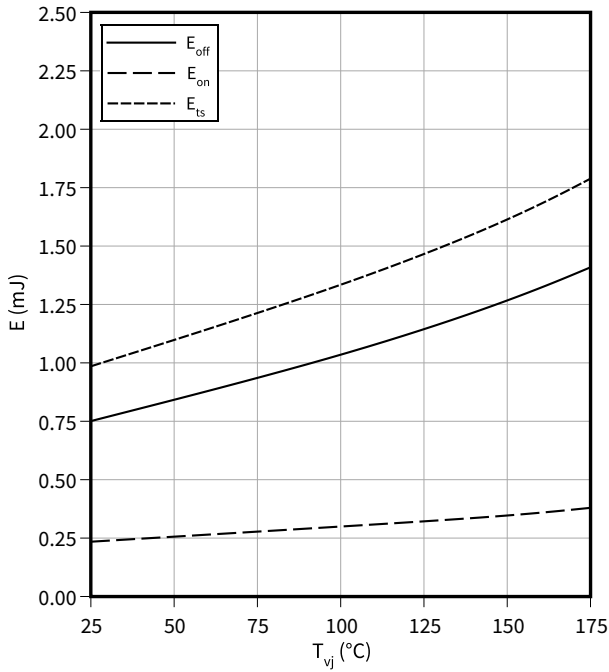


4 Characteristics diagrams

**Typical switching energy losses as a function of junction temperature**

$E = f(T_{vj})$

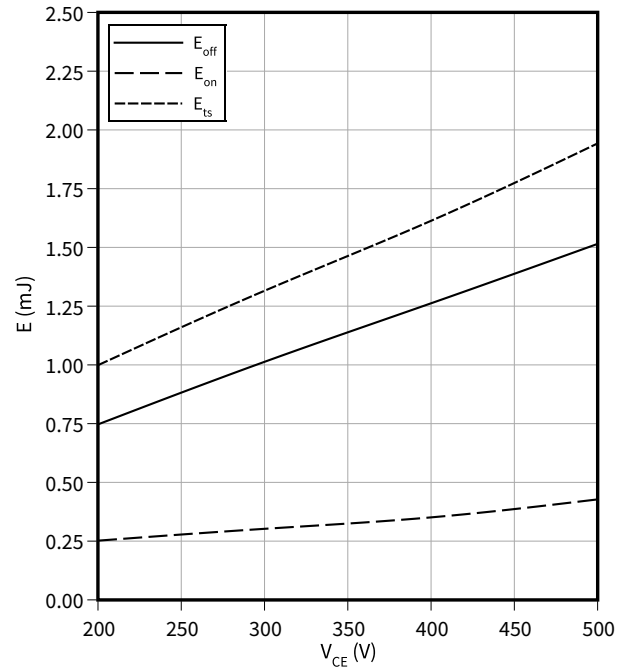
$I_C = 75 \text{ A}, V_{CC} = 400 \text{ V}, V_{GE} = 0/15 \text{ V}, R_G = 5.6 \Omega$



**Typical switching energy losses as a function of collector emitter voltage**

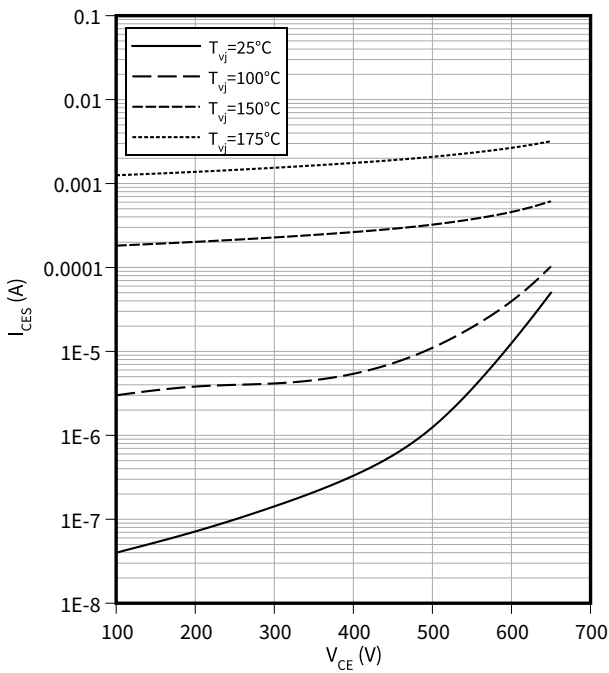
$E = f(V_{CE})$

$I_C = 75 \text{ A}, T_{vj} = 150 \text{ °C}, V_{GE} = 0/15 \text{ V}, R_G = 5.6 \Omega$



**Typ. reverse current vs. reverse voltage as a function of Tvj**

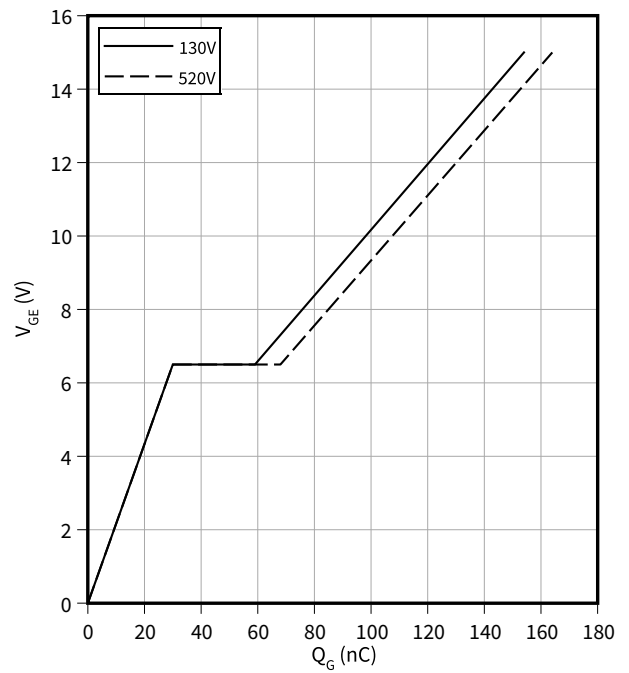
$I_{CES} = f(V_{CE})$



**Typical gate charge**

$V_{GE} = f(Q_G)$

$I_C = 75 \text{ A}$

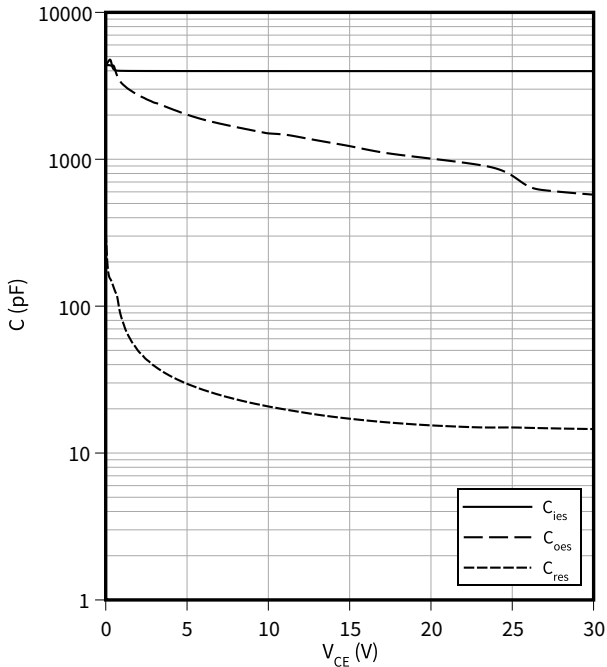


4 Characteristics diagrams

**Typical capacitance as a function of collector-emitter voltage**

$C = f(V_{CE})$

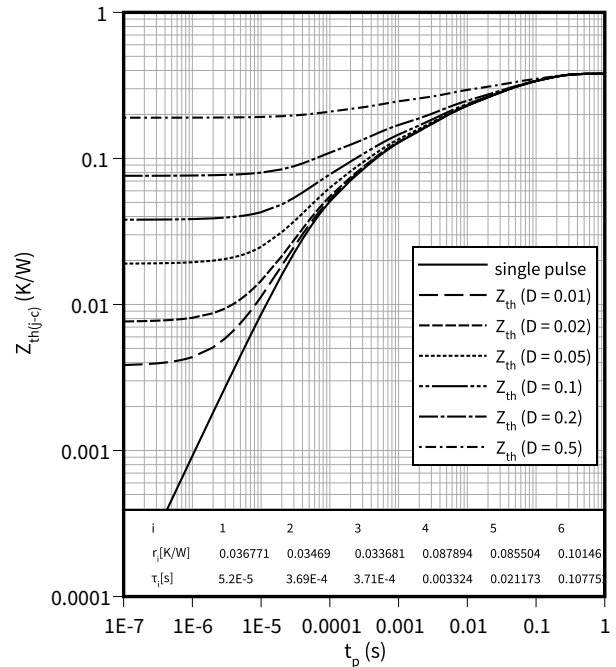
$f = 250 \text{ kHz}, V_{GE} = 0 \text{ V}$



**IGBT transient thermal impedance as a function of pulse width**

$Z_{th(j-c)} = f(t_p)$

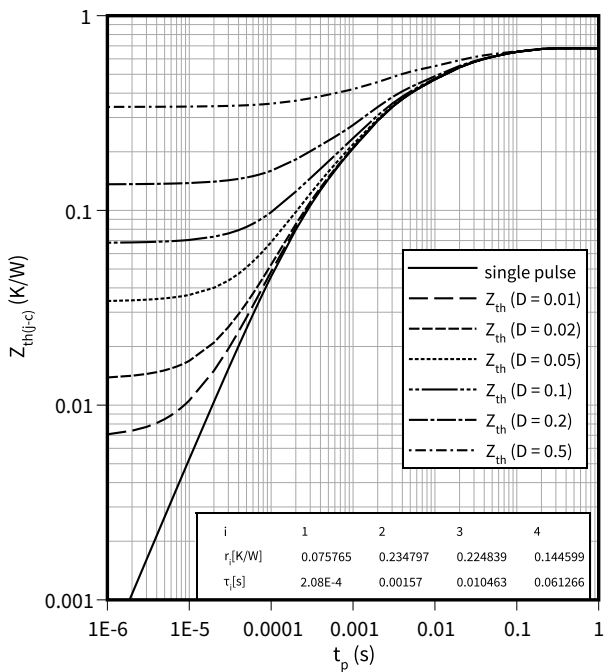
$D = t_p/T$



**Diode transient thermal impedance as a function of pulse width**

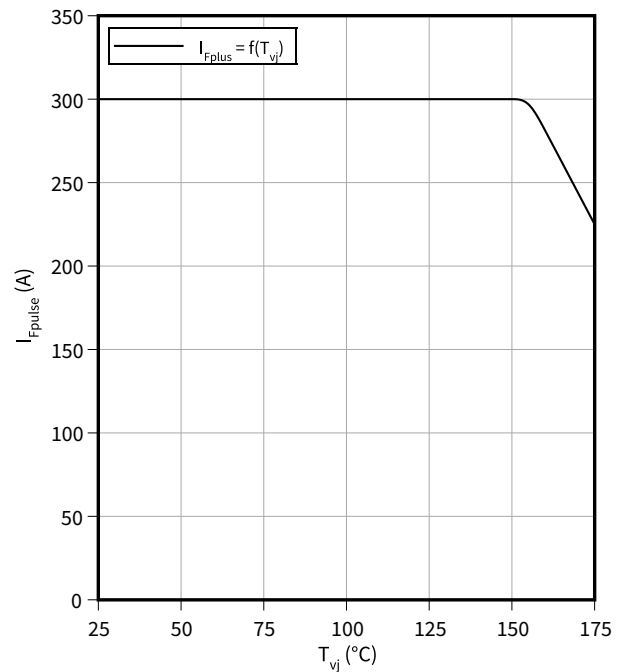
$Z_{th(j-c)} = f(t_p)$

$D = t_p/T$



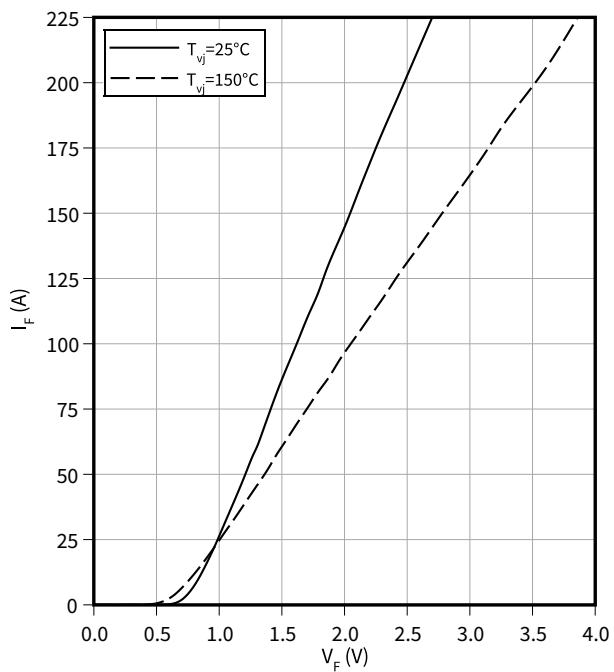
**Maximum pulse current as a function of junction temperature**

$I_{Fpulse} = f(T_{vj})$



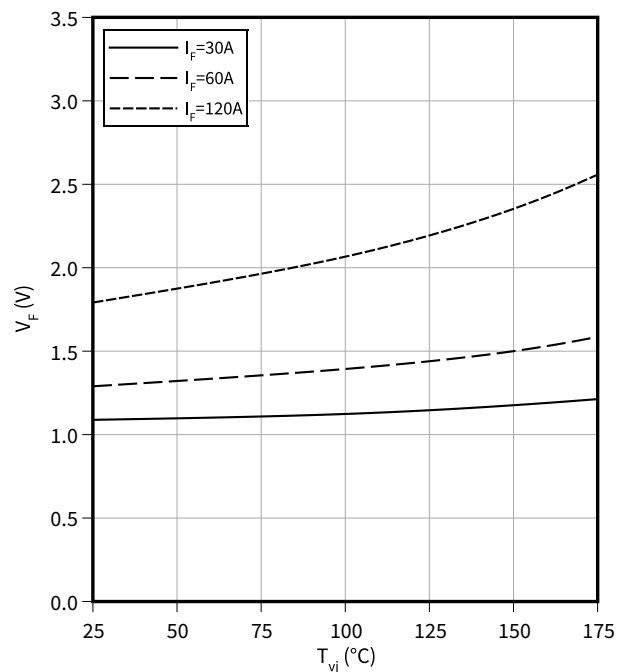
**Typical diode forward current as a function of forward voltage**

$I_F = f(V_F)$



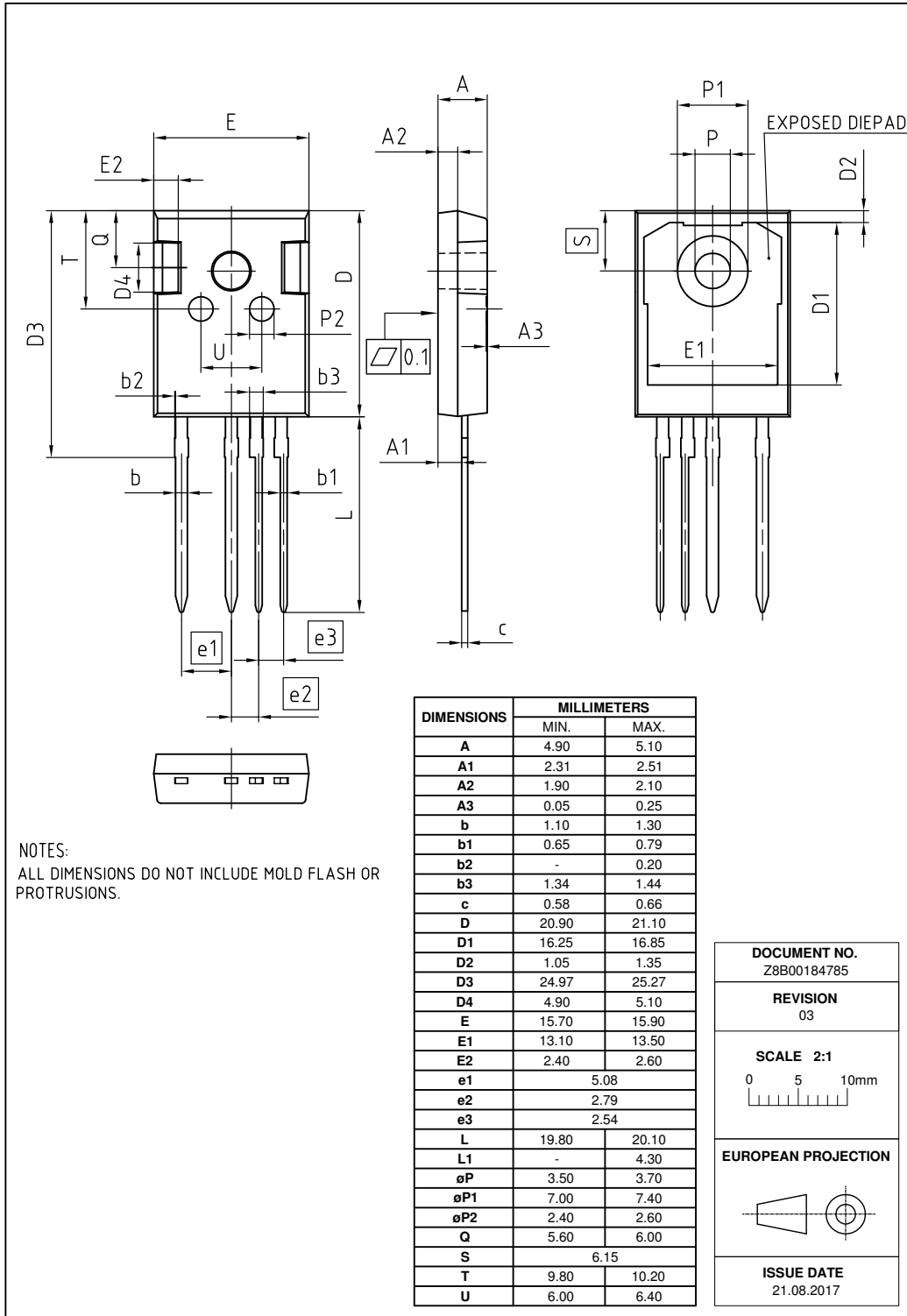
**Typical diode forward voltage as a function of junction temperature**

$V_F = f(T_{vj})$



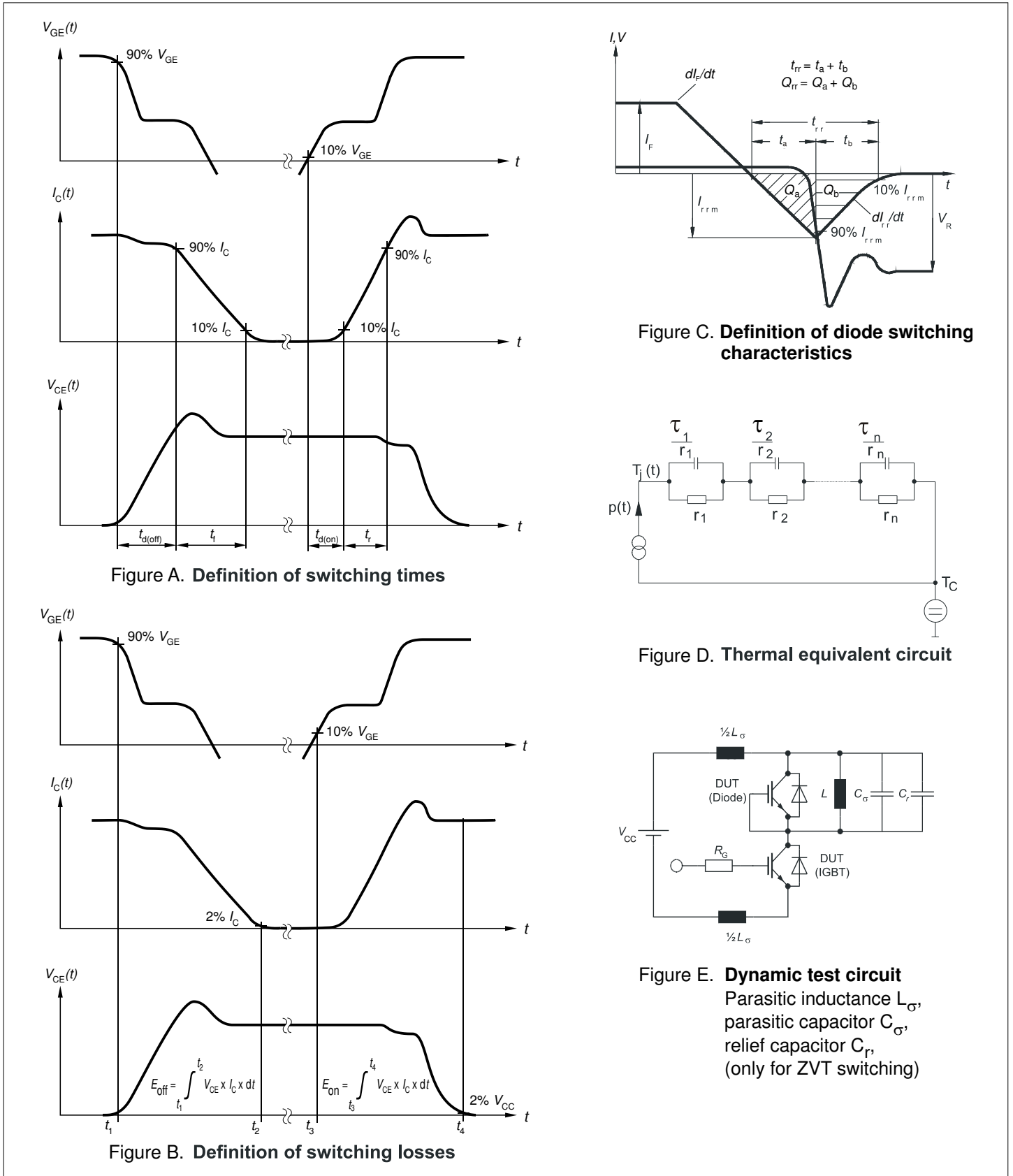
**5 Package outlines**

**PG-TO247-4-3**



**Figure 1**

**6 Testing conditions**



**Figure 2**

## Revision history

Document revision	Date of release	Description of changes
V1.1	2020-03-20	Preliminary data sheet
V2.1	2020-07-27	Final Data Sheet
V2.2	2020-07-29	Additional specification of internal emitter inductance
n/a	2020-11-30	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.10	2022-09-22	Rename of product family name from “Hybrid CoolSiC™ IGBT” to “CoolSiC™ hybrid discrete”

## Trademarks

All referenced product or service names and trademarks are the property of their respective owners.

**Edition 2022-09-22**

**Published by**

**Infineon Technologies AG**

**81726 Munich, Germany**

**© 2022 Infineon Technologies AG**

**All Rights Reserved.**

**Do you have a question about any aspect of this document?**

**Email: [erratum@infineon.com](mailto:erratum@infineon.com)**

**Document reference**

**IFX-AAL371-004**

## Important notice

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

Please note that this product is not qualified according to the AEC Q100 or AEC Q101 documents of the Automotive Electronics Council.

## Warnings

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.